



MOCD207M, MOCD208M Dual Channel Phototransistor Small Outline Surface Mount Optocouplers

Features

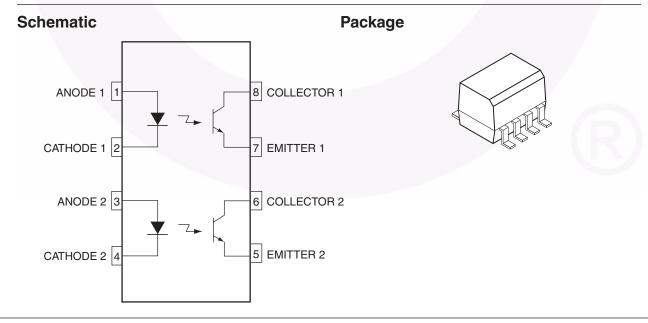
- Dual channel optocoupler
- Convenient plastic SOIC-8 surface mountable package style
- Two channels in one compact surface mount package
- Closely matched current transfer ratios to minimize unit-to-unit variation
- Minimum V_{(BR)CEO} of 70 volts guaranteed
- Standard SOIC-8 footprint, with 0.050" lead spacing
- Compatible with dual wave, vapor phase and IR reflow soldering
- High input-output isolation of 2500 Vac (rms) guaranteed
- Meets U.L. regulatory requirements, file #E90700, volume 2

Applications

- Feedback control circuits
- Interfacing and coupling systems of different potentials and impedances
- General purpose switching circuits
- Monitor and detection circuits

Description

The MOCD207M/MOCD208M consist of two silicon phototransistors optically coupled to two GaAs infrared LEDs. These devices are constructed in a small outline surface mount package which conforms to the standard SOIC-8 footprint.



Absolute Maximum Ratings ($T_A = 25^{\circ}C$ unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Rating	Value	Unit
EMITTER			
١ _F	Forward Current – Continuous	60	mA
I _F (pk)	Forward Current – Peak (PW = 100µs, 120pps)	1.0	А
V _R	Reverse Voltage	6.0	V
P _D	LED Power Dissipation @ $T_A = 25^{\circ}C$ Derate above 25°C	90 0.8	mW mW/°C
DETECTOR			
V _{CEO}	Collector-Emitter Voltage	70	V
V _{CBO}	Collector-Base Voltage	70	V
V _{ECO}	Emitter-Collector Voltage	7.0	V
I _C	Collector Current-Continuous	150	mA
P _D	Detector Power Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	150 1.76	mW mW/°C
TOTAL DEVICE			
V _{ISO}	Input-Output Isolation Voltage ^{$(1, 2)$} (f = 60Hz, 1 min. Duration)	2500	Vac(rms)
P _D	Total Device Power Dissipation @ T _A = 25°C Derate above 25°C	250 2.94	mW mW/°C
T _A	Ambient Operating Temperature Range	-40 to +100	°C
T _{stg}	Storage Temperature Range	-40 to +125	°C
TL	Lead Soldering Temperature (1/16" from case, 10 sec. duration)	260	°C

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Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Unit
EMITTER			1	1		1	1
V _F	Input Forward Voltage	I _F = 30mA	All		1.25	1.55	V
I _R	Reverse Leakage Current	V _R = 6.0V	All		0.001	100	μA
С	Capacitance		All		18		pF
DETECTO	DR						
I _{CEO}	Collector-Emitter Dark Current	$V_{CE} = 10V, T_A = 25^{\circ}C$	All		1.0	50	nA
I _{CEO}		$V_{CE} = 10V, T_A = 100^{\circ}C$	All		1.0		μA
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 100μΑ	All	70	100		V
V _{(BR)CEO}	Emitter-Collector Breakdown Voltage	I _E = 100μA	All	7.0	10		V
C _{CE}	Collector-Emitter Capacitance	$f = 1.0 \text{ MHz}, V_{CE} = 0 \text{V}$	All		7.0		pF
COUPLE	0						
	Current Transfer Ratio, Collector to Emitter ⁽⁴⁾	$I_{\rm F} = 10 {\rm mA}, V_{\rm CE} = 5 {\rm V}$	MOCD207M	100		200	%
			MOCD208M	40		125	
		$I_F = 1$ mA, $V_{CE} = 5$ V	MOCD207M	34			
			MOCD208M	13			
V _{CE (sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 2.0 {\rm mA}, I_{\rm F} = 10 {\rm mA}$	All			0.4	V
t _{on}	Turn-On Time	$I_{C} = 2.0 \text{mA}, V_{CC} = 10 \text{V}, \\ R_{L} = 100 \Omega$	All		3.0		μs
t _{off}	Turn-Off Time	$I_{C} = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_{L} = 100 \Omega$	All		2.8		μs
t _r	Rise Time	$I_{C} = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_{L} = 100 \Omega$	All		1.6		μs
t _f	Fall Time	$I_{C} = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_{L} = 100 \Omega$	All		2.2		μs
V _{ISO}	Isolation Surge Voltage ⁽¹⁾⁽²⁾	$ f = 60Hz, t = 1 min., \\ I_{I-O} \leq 2\mu A $	All	2500			Vac(rms)
R _{ISO}	Isolation Resistance ⁽²⁾	V _{I-O} = 500V	All	10 ¹¹			Ω
CISO	Isolation Capacitance ⁽²⁾	V _{I-O} = 0V, f = 1MHz	All		0.2		pF

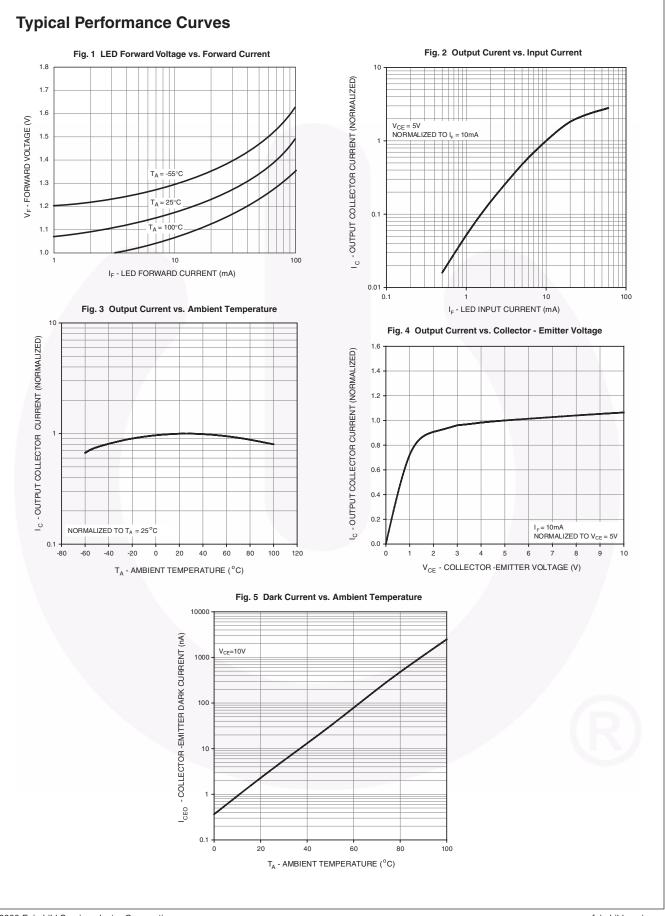
*Typical values at $T_A = 25^{\circ}C$

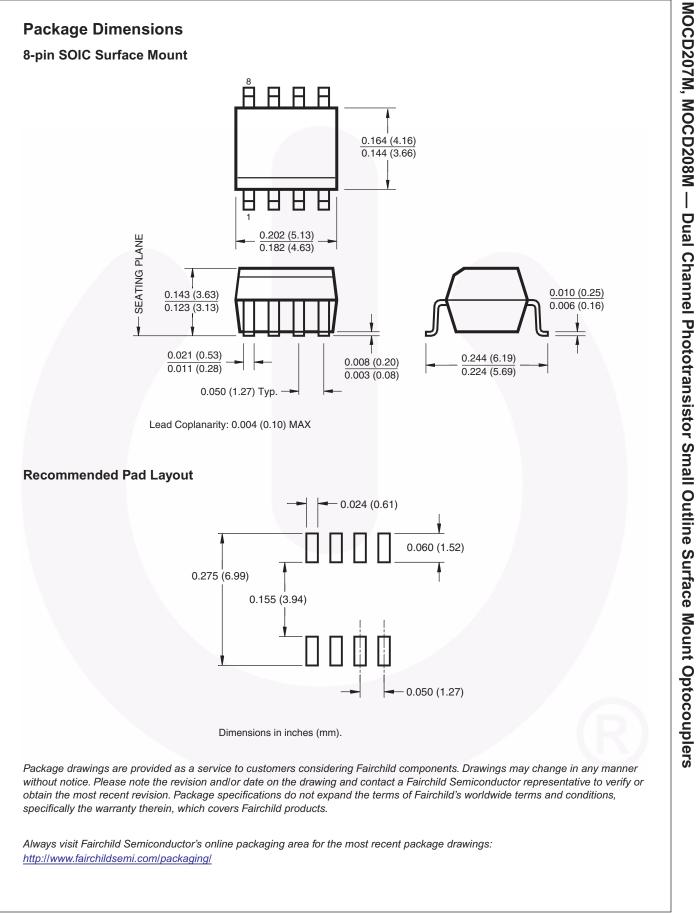
Note:

1. Input-Output Isolation Voltage, V_{ISO} , is an internal device dielectric breakdown rating.

- 2. For this test, Pins 1, 2, 3 and 4 are common and Pins 5, 6, 7 and 8 are common.
- 3. Always design to the specified minimum/maximum electrical limits (where applicable).

4. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

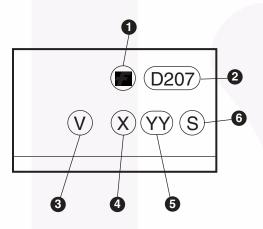




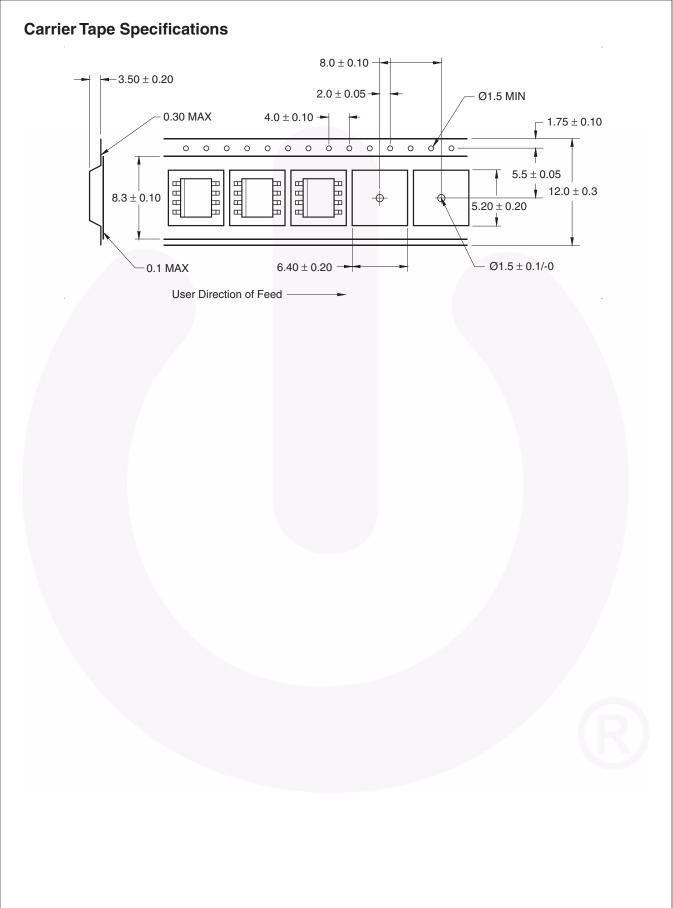
Ordering Information

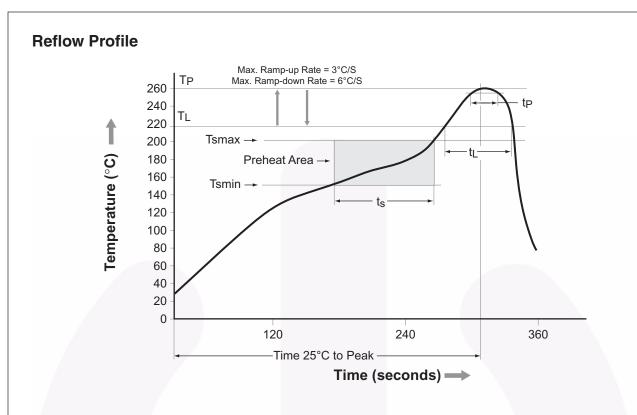
Option	Order Entry Identifier	Description
V	V	VDE Approved
D1	D1	Tape & Reel (500 units per reel), 16mm width carrier tape
D1V	D1V	VDE Approved, Tape & Reel (500 units per reel), 16mm width carrier tape
D2	D2	Tape & Reel (2500 units per reel), 16mm width carrier tape
D2V	D2V	VDE Approved, Tape & Reel (2500 units per reel), 16mm width carrier tape
R2	R2	Tape & Reel (2500 units per reel), 12mm width carrier tape
R2V	R2V	VDE Approved, Tape & Reel (2500 units per reel), 12mm width carrier tape

Marking Information



Definitions			
1	Fairchild logo		
2	Device number		
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)		
4	One digit year code, e.g., '3'		
5	Two digit work week ranging from '01' to '53'		
6	Assembly package code		





Profile Freature	Pb-Free Assembly Profile		
Temperature Min. (Tsmin)	150°C		
Temperature Max. (Tsmax)	200°C		
Time (t _S) from (Tsmin to Tsmax)	60–120 seconds		
Ramp-up Rate (t _L to t _P)	3°C/second max.		
Liquidous Temperature (T _L)	217°C		
Time (t_L) Maintained Above (T_L)	60–150 seconds		
Peak Body Package Temperature	260°C +0°C / -5°C		
Time (t _P) within 5°C of 260°C	30 seconds		
Ramp-down Rate (T _P to T _L)	6°C/second max.		
Time 25°C to Peak Temperature	8 minutes max.		



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